

Silicon NPN Power Transistors

BU408

DESCRIPTION

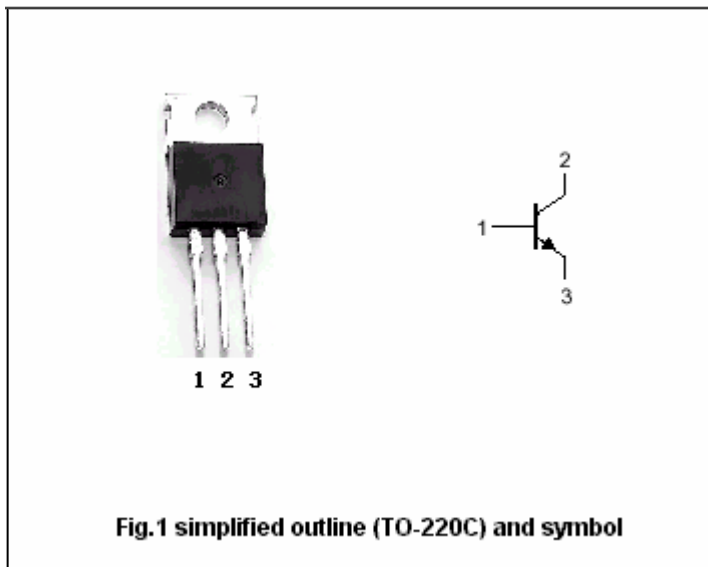
- With TO-220C package
- High voltage
- Fast switching speed

APPLICATIONS

- For use in horizontal deflection output stages of TV's and CTV's circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	400	V
$V_{CEO}$	Collector-emitter voltage	Open base	200	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current (DC)		7	A
$I_{CM}$	Collector current (Pulse)		10	A
$I_B$	Base current		4	A
$P_C$	Collector power dissipation	$T_C=25$	60	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55-150	

## Silicon NPN Power Transistors

BU408

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	200			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =5V	40			
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =250V ; V <sub>BE</sub> =0 T <sub>C</sub> =150			0.1 1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V ; I <sub>C</sub> =0			1	mA
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V	10			MHz
t <sub>off</sub>	Turn-off time	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			0.4	μs

Silicon NPN Power Transistors

BU408

PACKAGE OUTLINE

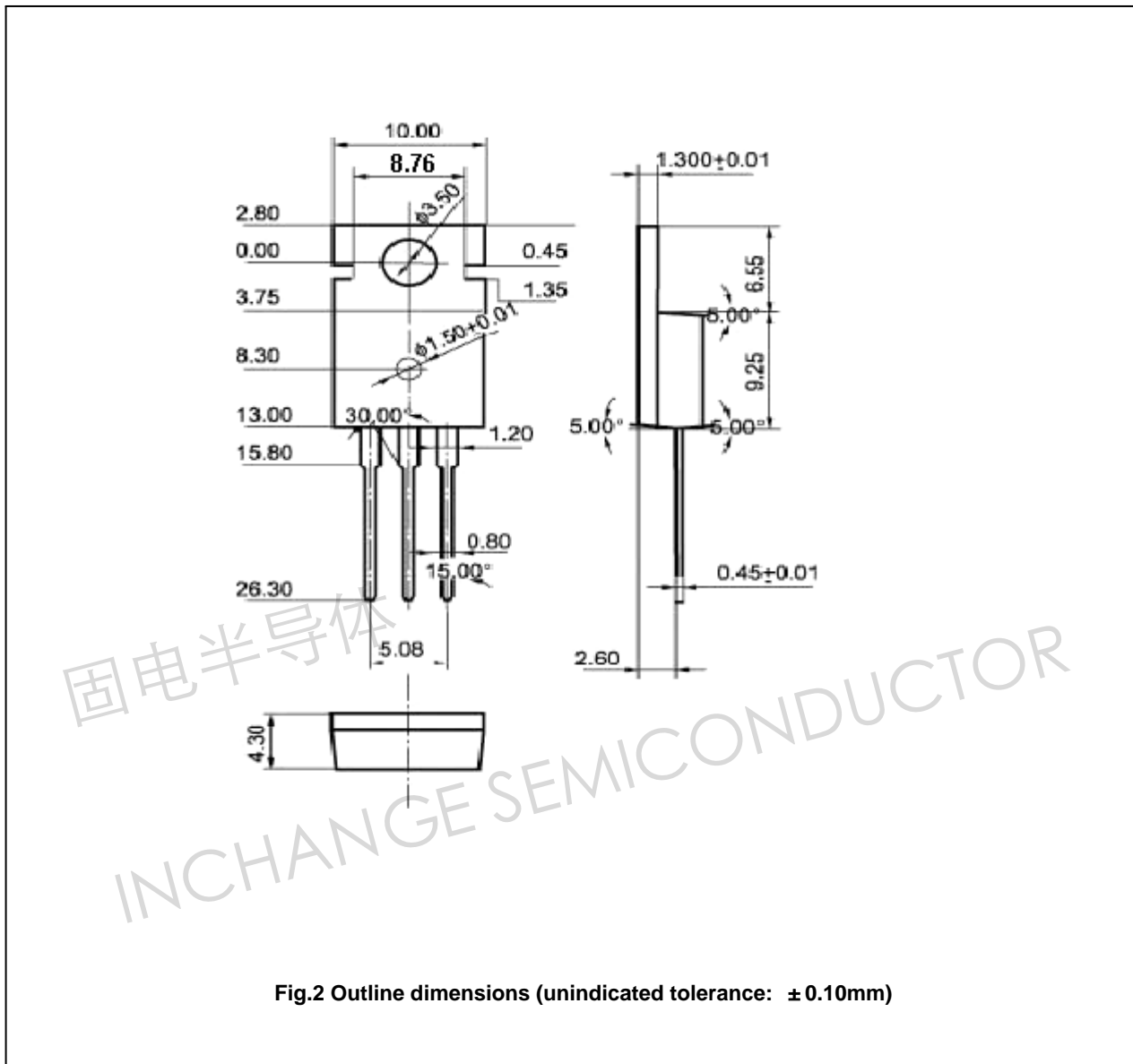


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)